

SANYO	No.695G	2SK242
		N-Channel Junction Silicon FET

High-Frequency General-Purpose Amp Applications

Features

- Ultrasmall-sized package permitting 2SK242-applied sets to be made small and slim.
- Small Crss (Crss=0.04pF typ).

Absolute Maximum Ratings at Ta=25°C

			unit
Gate-to-Drain Voltage	V _{GDO}	-20	V
Gate Current	I _G	10	mA
Drain Current	I _D	20	mA
Allowable Power Dissipation	P _D	150	mW
Junction Temperature	T _j	125	°C
Storage Temperature	T _{stg}	-55 to +125	°C

Electrical Characteristics at Ta=25°C

		min	typ	max	unit
G-D Breakdown Voltage	V _{(BR)GDO} I _G = -10μA	-20			V
Gate Cutoff Current	I _{GSS} V _{GS} = -0.5V, V _{DS} = 0			-10	nA
Drain Current	I _{DSS} V _{DS} = 5V, V _{GS} = 0	0.6*		12.0*	mA
Cutoff Voltage	V _{GS(off)} V _{DS} = 5V, I _D = 10μA			-2.5	V
Forward Transfer Admittance	Y _{fs} (1) V _{DS} = 5V, V _{GS} = 0, f = 1kHz	2.0	6.0		mS
	Y _{fs} (2) V _{DS} = 5V, V _{GS} = 0, f = 100MHz	2.0	6.0		mS
Input Capacitance	C _{iss} V _{DS} = 5V, V _{GS} = 0, f = 1MHz		4.0		pF
Reverse Transfer Capacitance	Crss V _{DS} = 5V, V _{GS} = 0, f = 1MHz	0.04	0.15		pF
Output Capacitance	C _{oss} V _{DS} = 5V, V _{GS} = 0, f = 1MHz		4.0		pF
Power Gain	PG V _{DS} = 5V, V _{GS} = 0, f = 100MHz		24		dB
Noise Figure	NF See specified Test Circuit.	3.5	6.0		dB

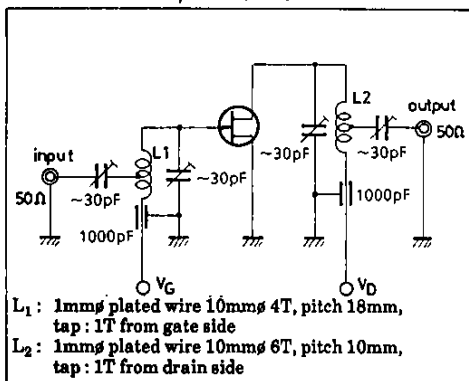
* : The 2SK242 is classified by I_{DSS} as follows : (unit : mA)

0.6	2	1.5	1.2	3	3.0	2.5	4	6.0	5.0	5	12.0
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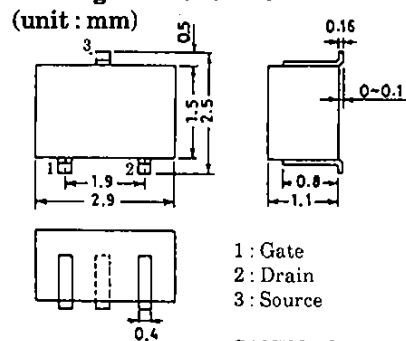
Note) Marking : T

I_{DSS} rank : 2, 3, 4, 5

PG, NF Test Circuit



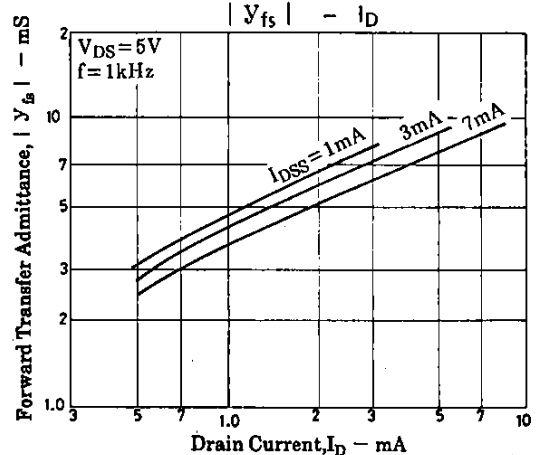
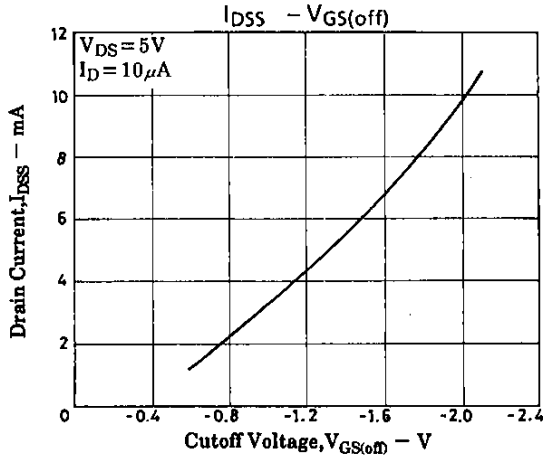
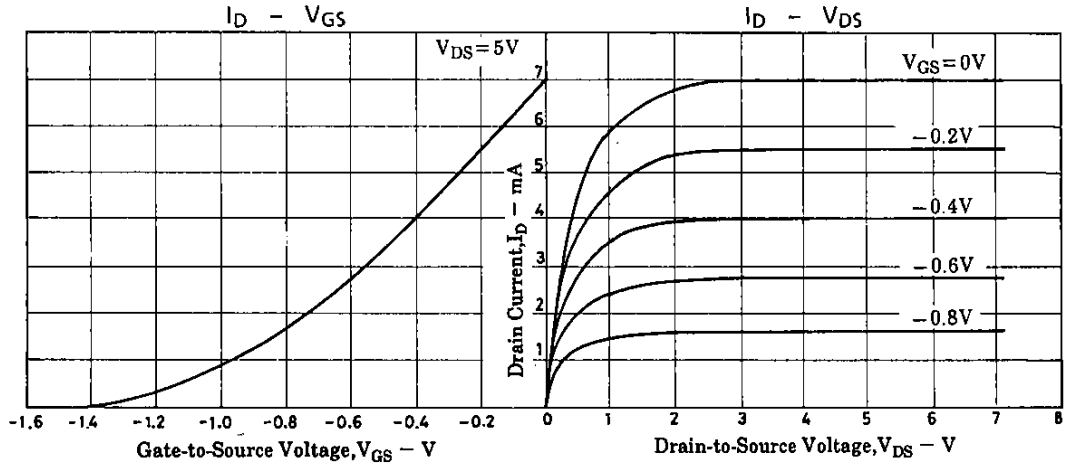
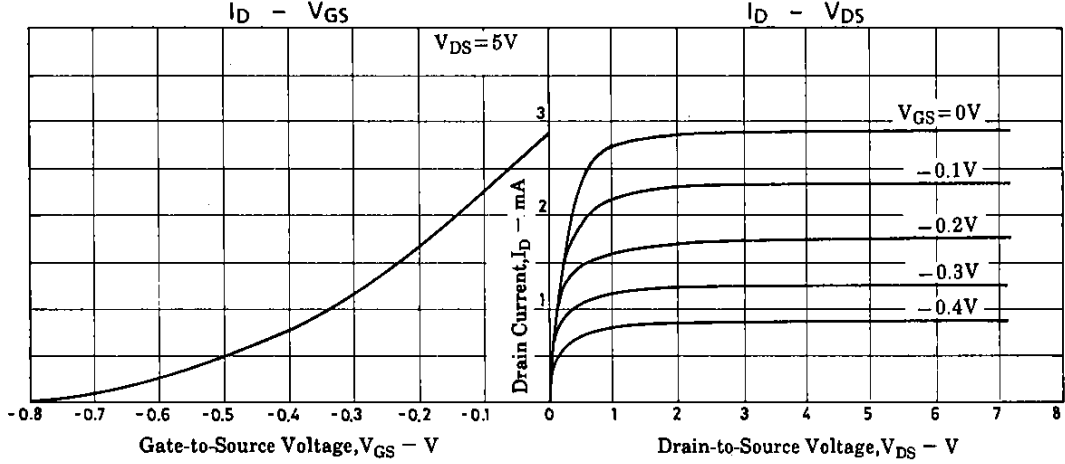
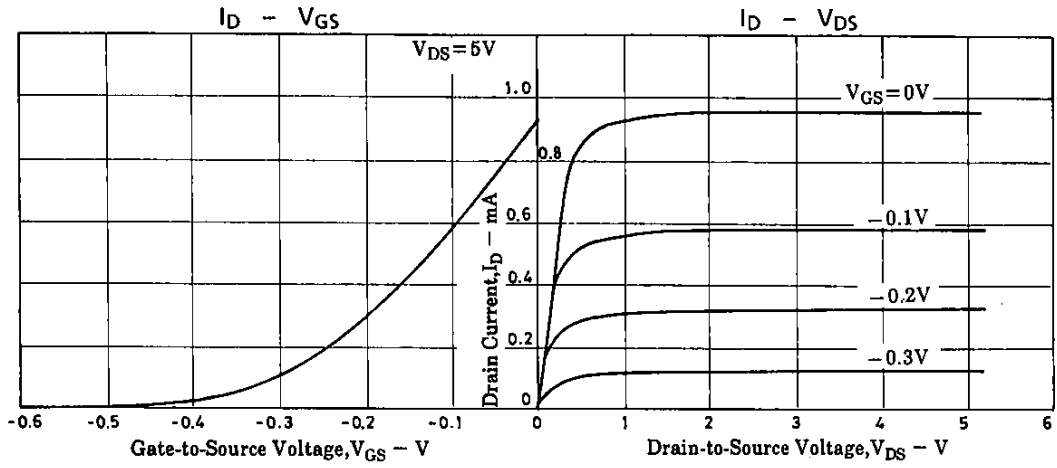
Package Dimensions 2024B

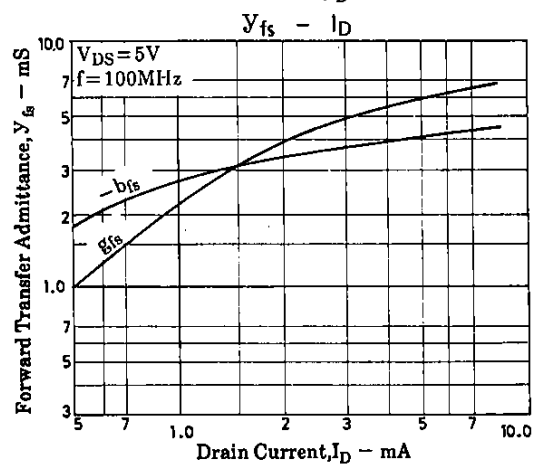
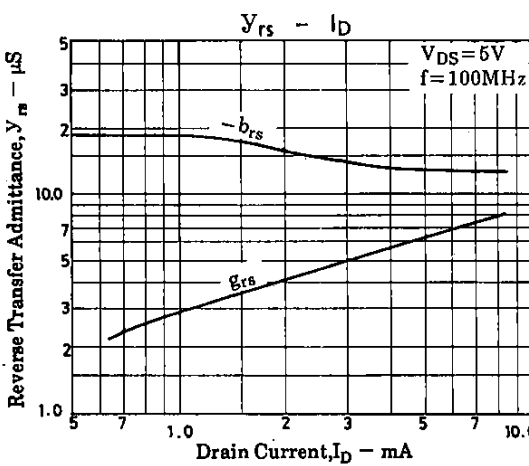
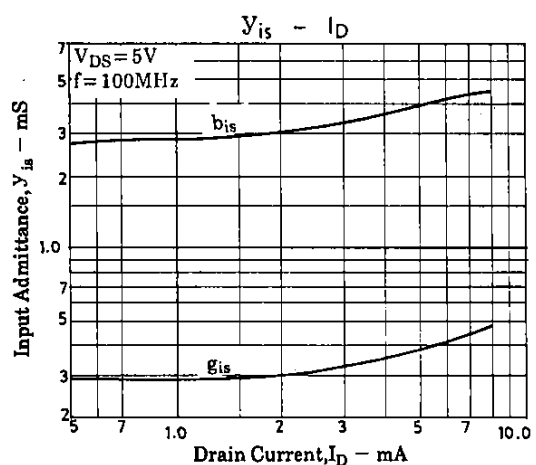
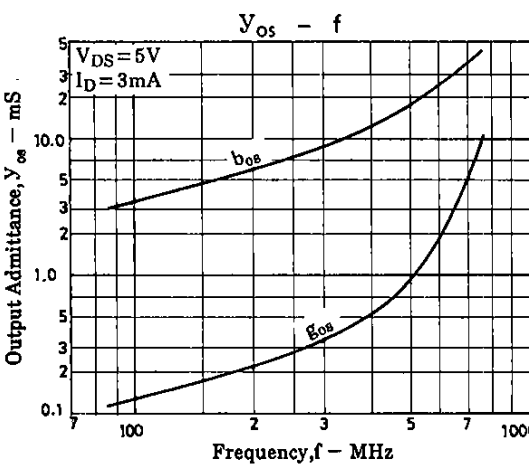
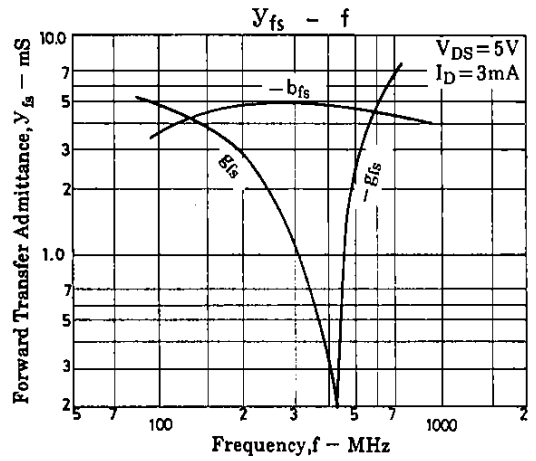
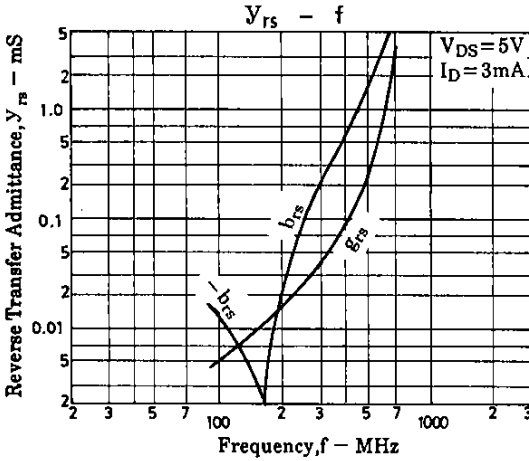
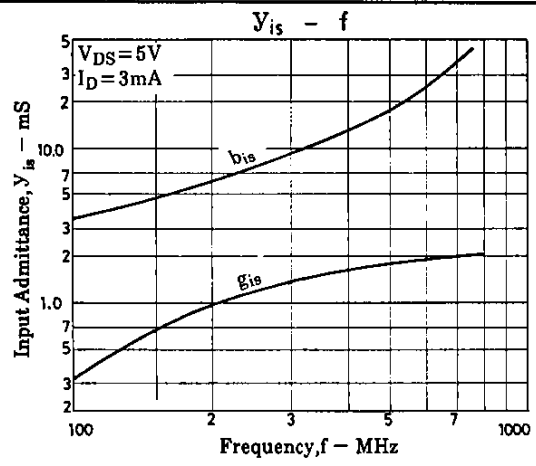
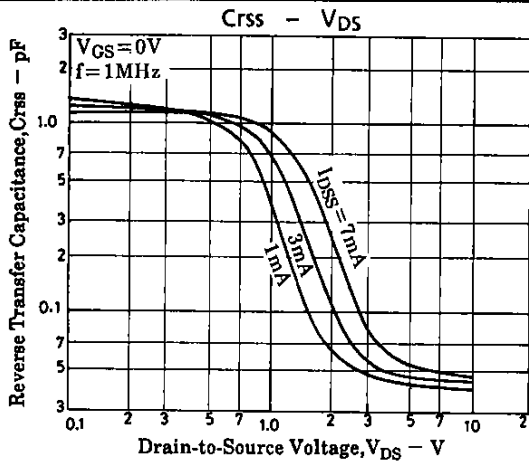


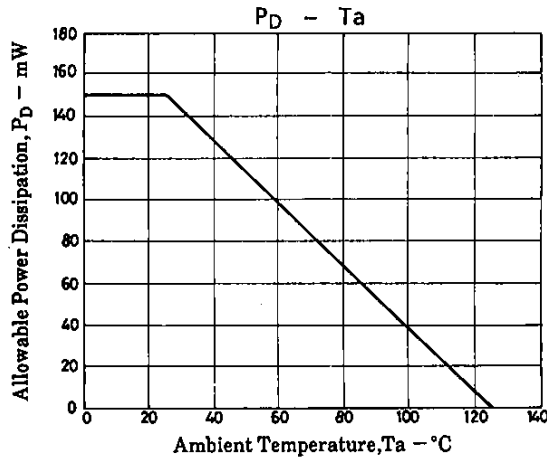
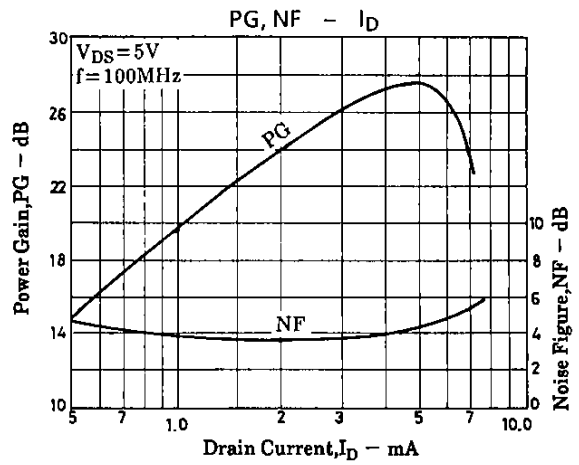
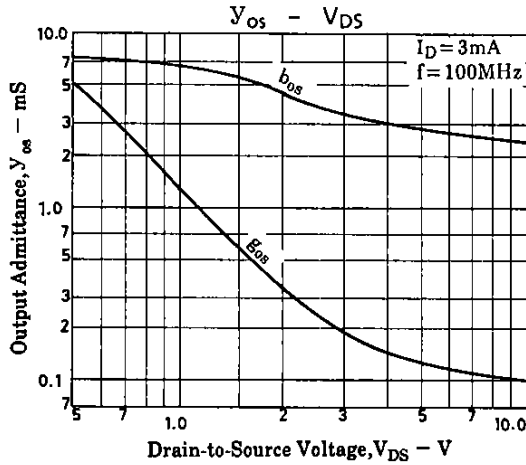
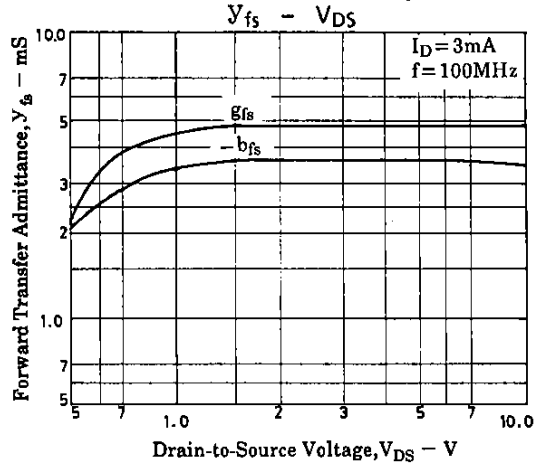
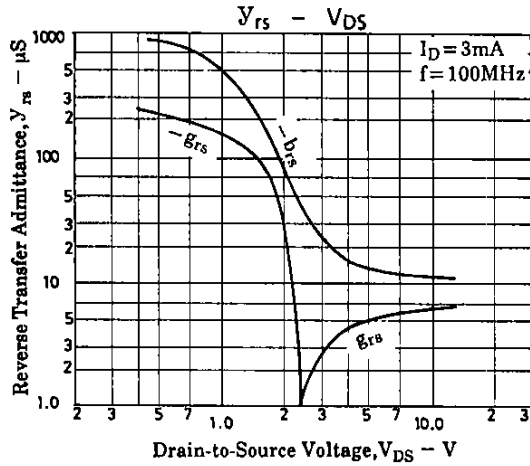
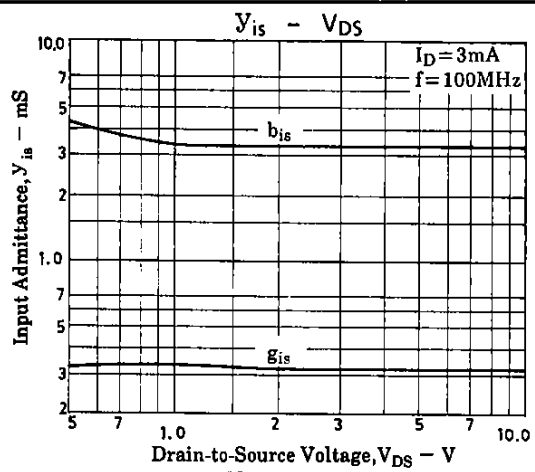
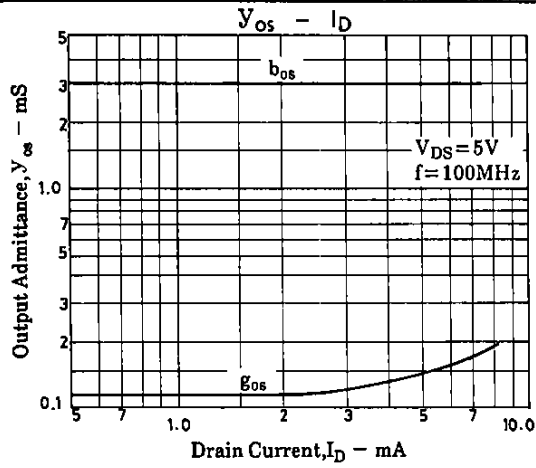
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